High-voltage Switching Transistor (Camera strobes and Telephone, Power supply) (-400V, -0.1A)

- 1) High breakdown voltage. (BVcEo=-400V)
- 2) Low saturation voltage, typically VCE(sat) = -0.2V at Ic / IB = -20mA / -2mA.
- 3) High switching speed, typically tf=1 μ s at lc=100mA.
- 4) Wide SOA (safe operating area).
- 5) Complements the 2SA4505.

Packaging specifications and hre

Туре	2SA1759
Package	MPT3
hee	Р
Marking	AH*
Code	T100
Basic ordering unit (pieces)	3000

* Denotes her

■ Electrical characteristics (Ta=25°C)

■ Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Collector-base voltage	Vсво	-400	V	
Collector-emitter voltage	VCEO	-400	V	
Emitter-base voltage	VEBO	-7	V	
Calla stan auronat	Ic	-0.1	A(DC)	
Collector current	IC	-0.2	A (Pulse) *1	
Collector power dissipation	Po	0.5	144	
	Pc	2 *2	W	
Junction temperature	Tj	150	°C	
Storage temperature	Tstg	-55~+150	°C	

^{*1} Single pulse, Pw=100ms

^{*2} When mounted on a 40×40×0.7 mm ceramic board

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	-400	_		V	Ic=-50 μ A
Collector-emitter breakdown voltage	BVceo	-400	_	_	V	Ic=-1mA
Emitter-base breakdown voltage	BVEBO	- 7	_		V	I _E =-50 μ A
Collector cutoff current	Ісво	_	_	-10	μΑ	VcB=-400V
Emitter cutoff current	Ієво	_	_	-10	μА	V _{EB} =-6V
Collector-emitter saturation voltage	VCE(sat)	_	-0.2	-0.5	V	Ic/IB=-20mA/-2mA
Base-emitter saturation voltage	VBE(sat)	_	_	-1.2	V	Ic/IB=-20mA/-2mA
DC current transfer ratio	hre	82	_	180	_	Vce=-10V, lc=-10mA
Transition frequency	f⊤	_	12	_	MHz	VcE=-10V, IE=10mA, f=5MHz
Output capacitance	Cob	_	13	_	pF	VcB=-10V , IE=0A , f=1MHz
Turn-on time	ton	_	0.7	_	μs	Ic=-100mA RL=1.5kΩ
Storage time	tstg	_	1.8	_	μs	I _{B1} =-I _{B2} =-10mA
Fall time	tr	_	1	_	μS	Vcc <u>~</u> −150V

(96-97-A324)

Power Transistor (400V, 0.1A)

2SC4505 / 2SC4620

Features

- 1) High breakdown voltage. (BVcEo=400V)
- 2) Low saturation voltage, typically VcE(sat) =0.05V at Ic / Ib=10mA / 1mA.
- 3) High switching speed, typically tf=1.7 μs at Ic=100mA
- 4) Complements the 2SC4505 and the 2SA1759.

Packaging specifications and hre

Type	2SC4505	2SC4620
Package	MPT3	ATV
hre	PQ	Q
Marking	CE*	_
Code	T100	TV2
Basic ordering unit (pieces)	1000	2500

■ Absolute maximum ratings (Ta=25°C)

Parame	ter	Symbol	Limits	Unit	
Collector-base volt	age	Vceo	400	V	
Collector-emitter ve	oltage	Vceo	400	V	
Emitter-base voltage		VEBO	7	V	
Collector current		lc	0.1	A	
		ICP	0.2	A *	
Collector power dissipation	2SC4505	_	0.5	1.1	
	2SC4620	Pc	1	W	
Junction temperatu	Junction temperature		150	ů	
Storage temperature		Tstg	-55~ + 150	Ĉ	

^{*} Single pulse Pw=20ms Duty=1 / 2

■ Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	400	_	_	V	Ic=50 μ A
Collector-emitter breakdown voltage	BVceo	400	_	_	V	Ic=1mA
Emitter-base breakdown voltage	ВУево	7	_	_	V	Iε=50 μ A
Collector cutoff current	Ісво	_	_	10	μА	Vcs=400V
Emitter cutoff current	lebo	_	_	10	μА	VEB=6V
Collector-emitter saturation voltage	VCE(sat)	_	0.05	0.5	V	Ic=10mA , Is=1mA
Base-emitter saturation voltage	VBE(sat)	_	_	1.5	V	Ic=10mA , Is=1mA
DC eurrent transfer ratio	hfe	82	_	270	_	Vce/lc=10V/10mA
Transition frequency	f⊤	_	20	_	MHz	VcE=10V , IE=-10mA , f=10MHz
Optput capacitance	Cob	_	7	_	pF	Vcs=10V, IE=0A, f=1MHz
Tuen-on time	ton	_	1	_	μs	Ic=100mA
Storage time	tsig	_	5.5	_	μs	I _{B1} =-I _{B2} =10mA
Fall time	tf	_	1.7	_	μS	Vcc~-150V

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